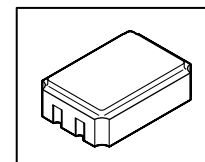


TECHNICAL DATA
DATA SHEET 5032, REV. A**HERMETIC POWER MOSFET
N-CHANNEL**

SHD246723S -- S-100 (JANTX) Screening

**FEATURES:**

- 60 Volt, 1.6 Ohm, 0.3 A MOSFET
- Isolated Hermetic, Ceramic Package
- Fast Switching
- Low $R_{DS(on)}$

MAXIMUM RATINGSALL RATINGS ARE AT $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
DRAIN TO SOURCE VOLTAGE	V_{DS}	-	-	60	Volts
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	± 20	Volts
ON-STATE DRAIN CURRENT @ $T_C = 25^\circ\text{C}$	$I_{D(on)}$	-	-	0.3	Amps
PULSED DRAIN CURRENT @ $T_C = 25^\circ\text{C}$	I_{DM}	-	-	3.0	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+150	$^\circ\text{C}$
TOTAL DEVICE DISSIPATION @ $T_C = 25^\circ\text{C}$	P_D	-	-	1250	mW
THERMAL RESISTANCE, JUNCTION TO CASE	R_{thJC}	-	-	100	$^\circ\text{C}/\text{W}$

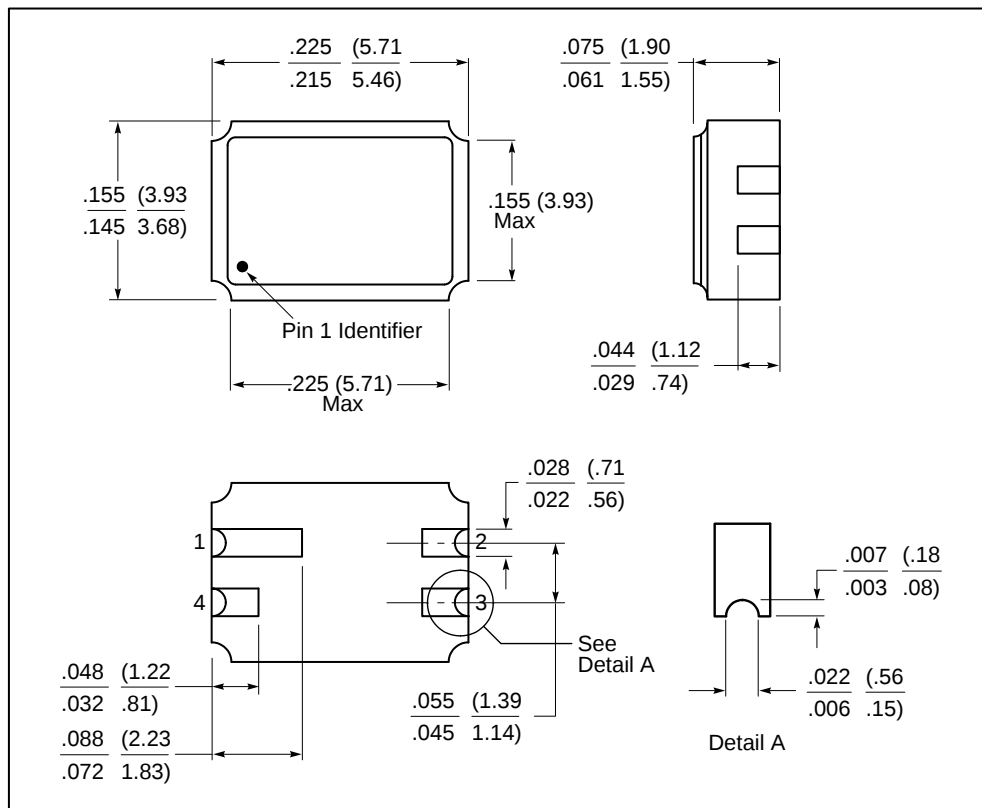
ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0\text{V}, I_D = 0.1\text{ mA}$	BV_{DSS}	60	-	-	Volts
STATIC DRAIN TO SOURCE ON STATE RESISTANCE Pulse width = 300 μs , Duty cycle $\leq 2\%$ $V_{GS} = 10\text{V}, I_D = 500\text{mA}$ $V_{GS} = 5\text{V}, I_D = 200\text{mA}$	$R_{DS(ON)}$	-	-	1.6 4.0	Ω
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}, I_D = 0.25\text{ mA}$	$V_{GS(th)}$	1.0	-	2.5	Volts
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = 48\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$	I_{DSS}	-	-	10 100	μA
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 10\text{V}$ GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -10\text{V}$ $V_{DS} = 0\text{V}$	I_{GSS}	-	-	200 -200	nA
TURN ON TIME $V_{DD} = 30\text{V},$ $I_D = 200\text{mA},$	$t_{(ON)}$	-	25	-	nsec
TURN OFF $V_{GS} = 10\text{V}$	$t_{(OFF)}$	-	35	-	
INPUT CAPACITANCE OUTPUT CAPACITANCE REVERSE TRANSFER CAPACITANCE $V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{MHz}$	C_{iss} C_{oss} C_{rss}	-	30 7 3	-	pF

+

SENSITRON
DATA SHEET 5032
REV. -

MECHANICAL DIMENSIONS: in Inches / mm



LCC-4

PINOUTS

DEVICE TYPE	PIN 1	PIN 2	PIN 3	PIN 4
N-CHANNEL MOSFET IN A LCC-4 CERAMIC PACKAGE	DRAIN	SOURCE	GATE	N/C

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